

UNCLAMPED COLLECTOR-TO-EMITTER AVALANCHE CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Single Pulse Collector-to-Emitter Avalanche Energy $V_{CC} = 50\text{ V}$, $V_{GE} = 5.0\text{ V}$, $Pk\ I_L = 9.5\text{ A}$, $R_G = 1\text{ k}\Omega$, $L = 3.5\text{ mH}$, Starting $T_C = 150^\circ\text{C}$	E_{AS}	158	mJ

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.0	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Maximum Temperature for Soldering Purposes, 1/8" from case for 5 seconds (Note 2)	T_L	275	$^\circ\text{C}$

- When surface mounted to an FR4 board using the minimum recommended pad size.
- For further details, see Soldering and Mounting Techniques Reference Manual: SOLDERM/D.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
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OFF CHARACTERISTICS (Note 3)

Collector-Emitter Clamp Voltage	BV_{CES}	$I_C = 2.0\text{ mA}$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	430	450	470	V
		$I_C = 10\text{ mA}$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	450	475	500	
		$I_C = 12\text{ A}$, $L = 3.5\text{ mH}$, $R_G = 1\text{ k}\Omega$ (Note 4)	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	420	450	480	
Collector-Emitter Leakage Current	I_{CES}	$V_{CE} = 15\text{ V}$, $V_{GE} = 0\text{ V}$	$T_J = 25^\circ\text{C}$		0.002	1.0	μA
		$V_{CE} = 250\text{ V}$, $R_G = 1\text{ k}\Omega$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	0.5	2.0	100	
Reverse Collector-Emitter Clamp Voltage	$BV_{CES(R)}$	$I_C = -75\text{ mA}$	$T_J = 25^\circ\text{C}$	30	33	39	V
			$T_J = 175^\circ\text{C}$	31	35	40	
			$T_J = -40^\circ\text{C}$	30	31	37	
Reverse Collector-Emitter Leakage Current	$I_{CES(R)}$	$V_{CE} = -24\text{ V}$	$T_J = 25^\circ\text{C}$	–	0.4	1.0	mA
			$T_J = 175^\circ\text{C}$	–	20	35	
			$T_J = -40^\circ\text{C}$	–	0.04	0.2	
Gate-Emitter Clamp Voltage	BV_{GES}	$I_G = \pm 5.0\text{ mA}$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	12	12.5	14	V
Gate-Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 5.0\text{ V}$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	200	316	350	μA
Gate Resistor	R_G		$T_J = -40^\circ\text{C to } 175^\circ\text{C}$		70		Ω
Gate-Emitter Resistor	R_{GE}		$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	14.25	16	25	$\text{k}\Omega$

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GE(th)}$	$I_C = 1.0\text{ mA}$, $V_{GE} = V_{CE}$	$T_J = 25^\circ\text{C}$	1.5	1.8	2.1	V
			$T_J = 175^\circ\text{C}$	0.7	1.0	1.3	
			$T_J = -40^\circ\text{C}$	1.7	2.0	2.3	
Threshold Temperature Coefficient (Negative)				4.0	4.6	5.2	$\text{mV}/^\circ\text{C}$
Collector-to-Emitter On-Voltage	$V_{CE(on)}$	$I_C = 10\text{ A}$, $V_{GE} = 3.7\text{ V}$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	0.8	1.11	1.97	V
		$I_C = 10\text{ A}$, $V_{GE} = 4.0\text{ V}$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	0.8	1.10	1.85	
		$I_C = 15\text{ A}$, $V_{GE} = 4.0\text{ V}$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	0.8	1.24	2.00	
Forward Transconductance	g_{fs}	$I_C = 6.0\text{ A}$, $V_{CE} = 5.0\text{ V}$	$T_J = 25^\circ\text{C}$	10	19	25	Mhos

DYNAMIC CHARACTERISTICS (Note 3)

Input Capacitance	C_{ISS}	$f = 10\text{ kHz}$, $V_{CE} = 25\text{ V}$	$T_J = 25^\circ\text{C}$	1100	1400	1600	pF
Output Capacitance	C_{OSS}			50	65	80	
Transfer Capacitance	C_{RSS}			15	20	25	

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
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SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time (Resistive) 10% V_{GE} to 10% I_C	$t_{d(on)R}$	$V_{CC} = 14\text{ V}, R_L = 1.0\ \Omega,$ $R_G = 1.0\text{ k}\Omega, V_{GE} = 5.0\text{ V}$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	0.1	1.0	2.0	μs
Rise Time (Resistive) 10% I_C to 90% I_C	t_{rR}		$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	1.0	3.4	6.0	
Turn-Off Delay Time (Resistive) 90% V_{GE} to 90% I_C	$t_{d(off)R}$	$V_{CC} = 14\text{ V}, R_L = 1.0\ \Omega,$ $R_G = 1.0\text{ k}\Omega, V_{GE} = 5.0\text{ V}$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	2.0	4.5	8.0	μs
Fall Time (Resistive) 90% I_C to 10% I_C	t_{fR}		$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	3.0	8.0	12	
Turn-Off Delay Time (Inductive) 90% V_{GE} to 90% I_C	$t_{d(off)L}$	$V_{CE} = BV_{CES}, L = 0.5\text{mH},$ $R_G = 1.0\text{ k}\Omega, I_C = 10\text{ A},$ $V_{GE} = 5.0\text{ V}$	$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	6.5	9.7	12.5	μs
Fall Time (Inductive) 90% I_C to 10% I_C	t_{fL}		$T_J = -40^\circ\text{C to } 175^\circ\text{C}$	6.0	8.3	11	

3. Electrical Characteristics at temperature other than 25°C , Dynamic and Switching characteristics are not subject to production testing.
4. Not subject to production testing.

TYPICAL ELECTRICAL CHARACTERISTICS

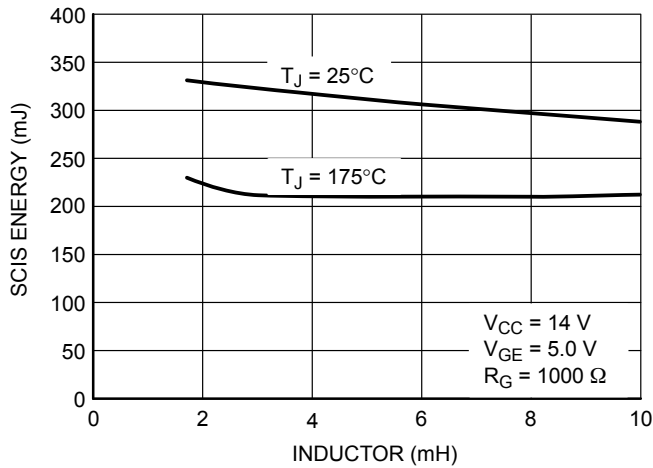


Figure 1. Self Clamped Inductive Switching

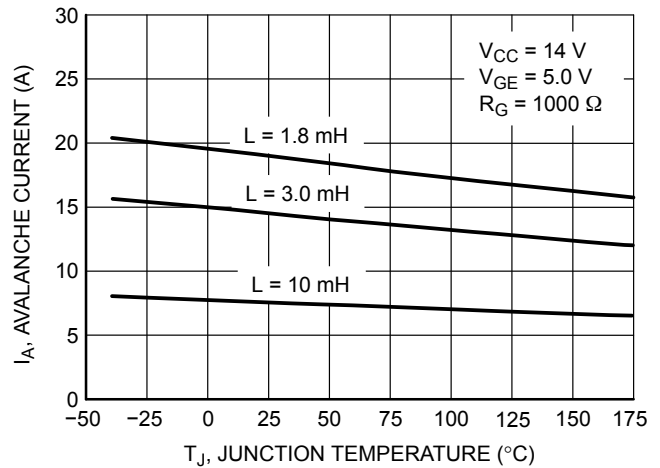


Figure 2. Open Secondary Avalanche Current vs. Temperature

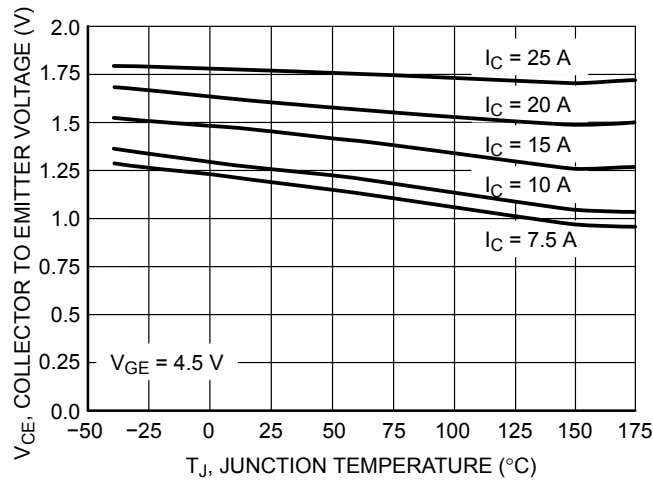


Figure 3. Collector-to-Emitter Voltage vs. Junction Temperature

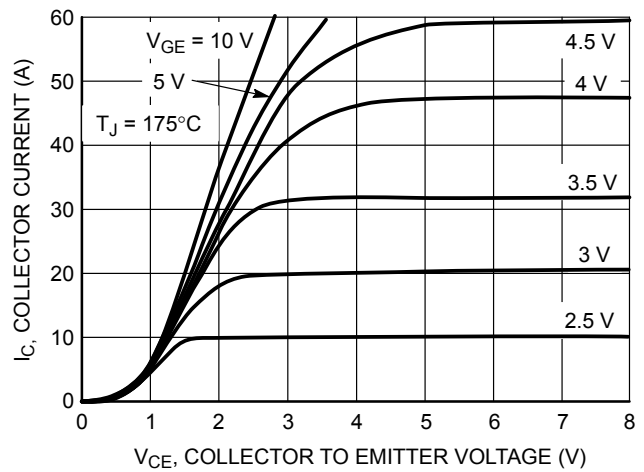


Figure 4. Collector Current vs. Collector-to-Emitter Voltage

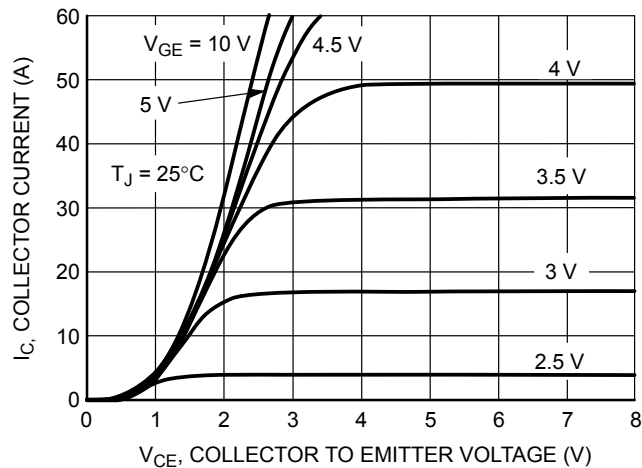


Figure 5. Collector Current vs. Collector-to-Emitter Voltage

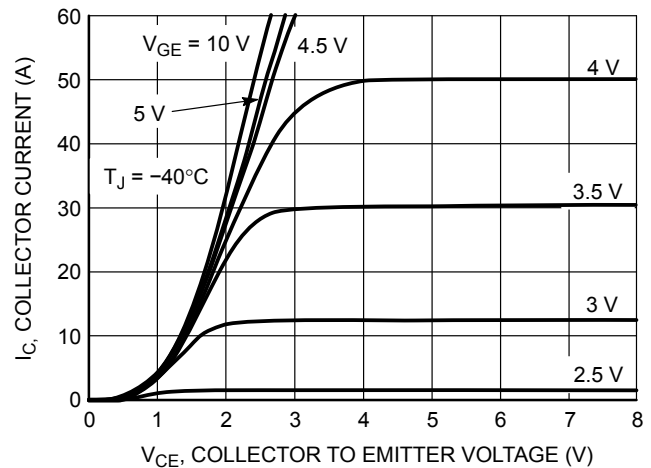


Figure 6. Collector Current vs. Collector-to-Emitter Voltage

TYPICAL ELECTRICAL CHARACTERISTICS

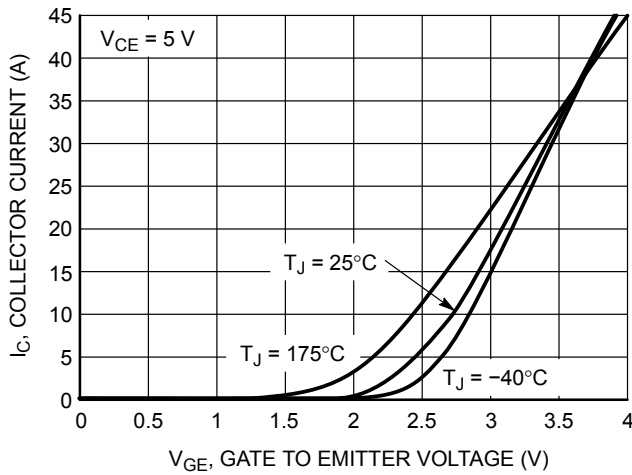


Figure 7. Transfer Characteristics

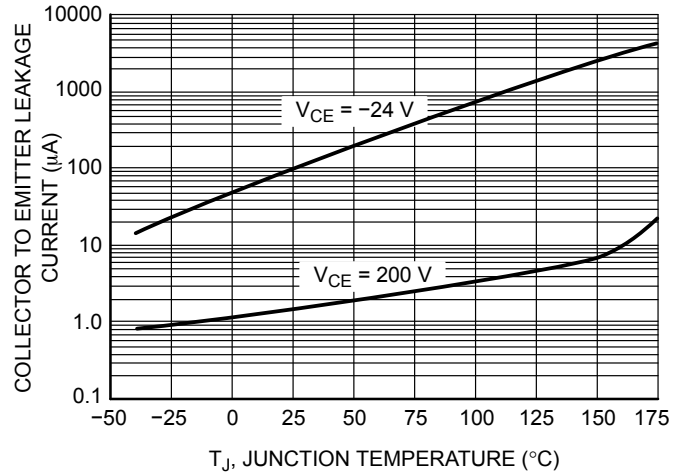


Figure 8. Collector-to-Emitter Leakage Current vs. Temperature

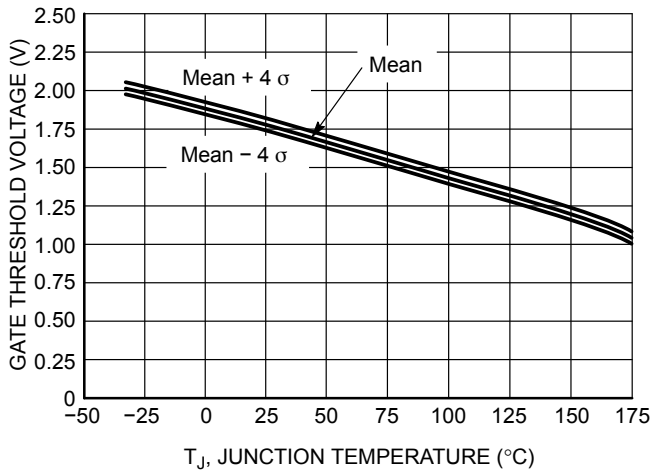


Figure 9. Gate Threshold Voltage vs. Temperature

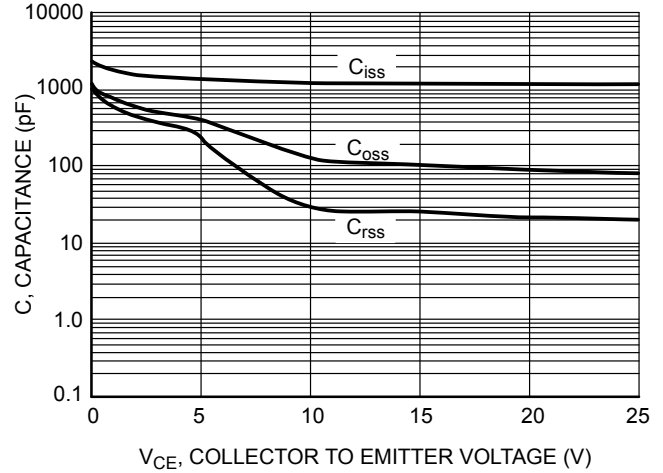


Figure 10. Capacitance vs. Collector-to-Emitter Voltage

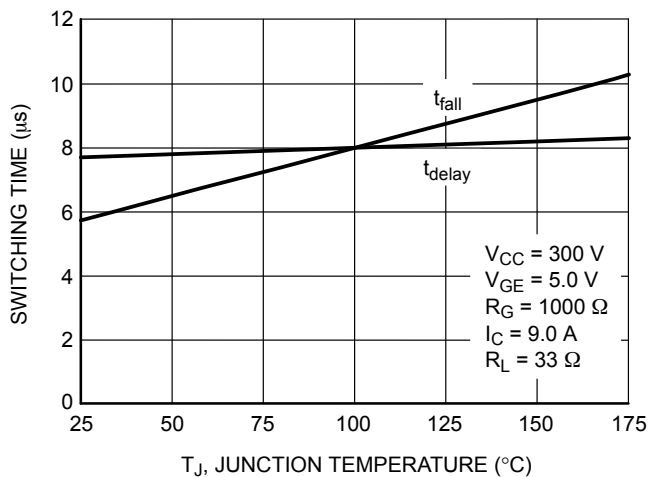


Figure 11. Resistive Switching Fall Time vs. Temperature

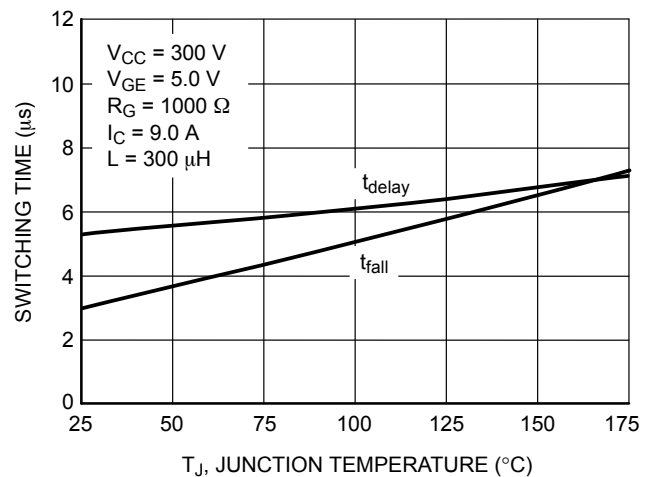
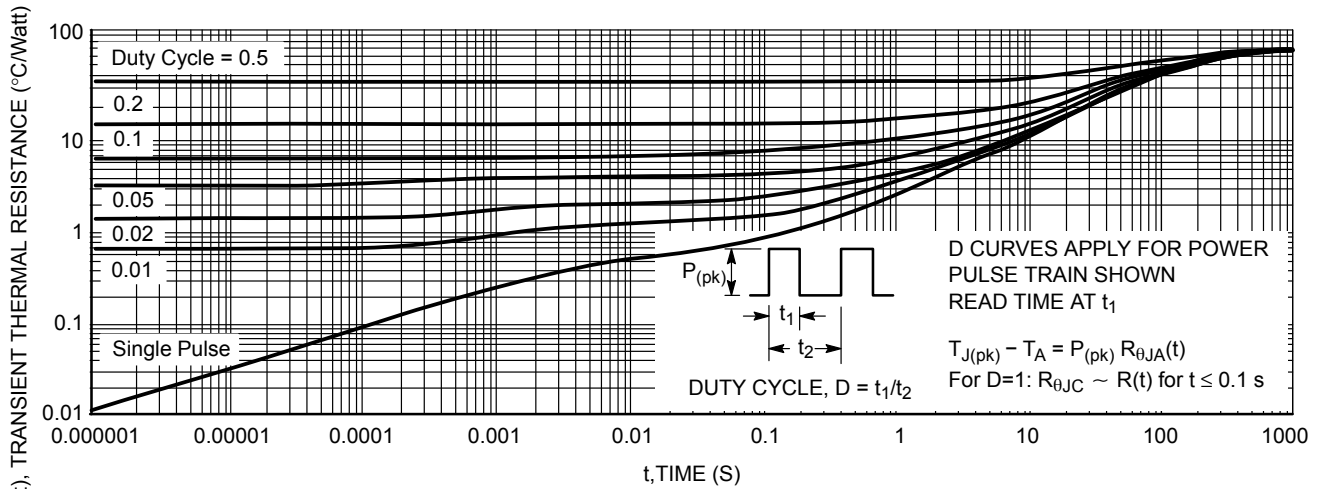
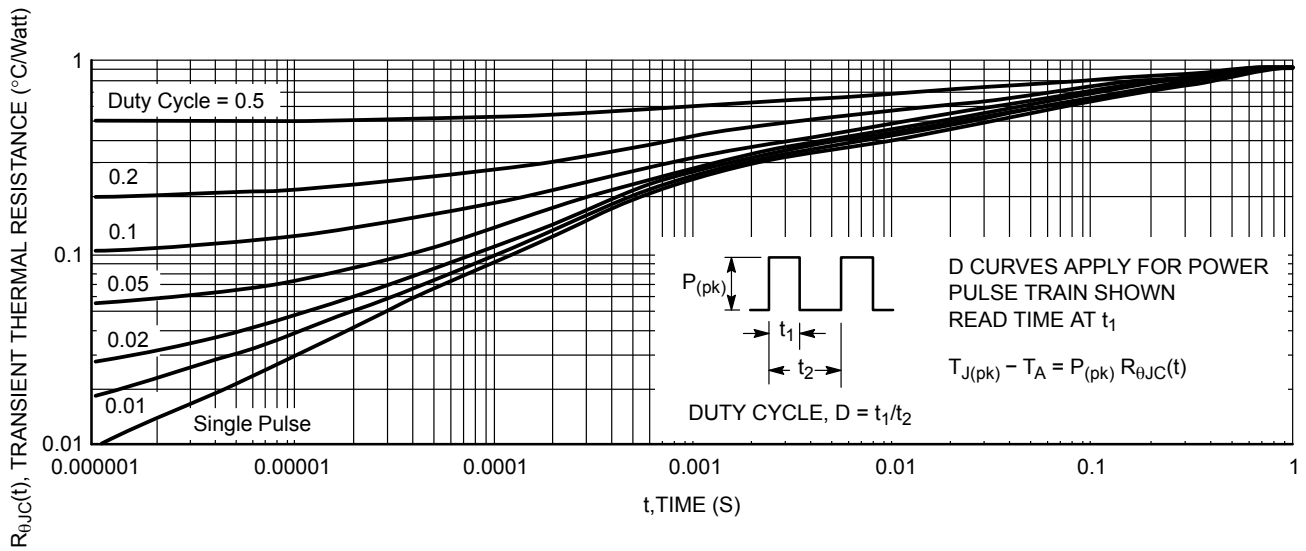


Figure 12. Inductive Switching Fall Time vs. Temperature



**Figure 13. Minimum Pad Transient Thermal Resistance
(Non-normalized Junction-to-Ambient)**

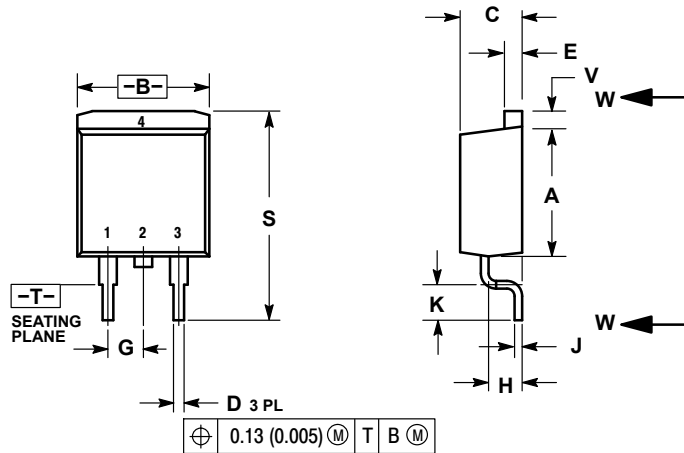


**Figure 14. Best Case Transient Thermal Resistance
(Non-normalized Junction-to-Case Mounted on Cold Plate)**

NGB8245N

PACKAGE DIMENSIONS

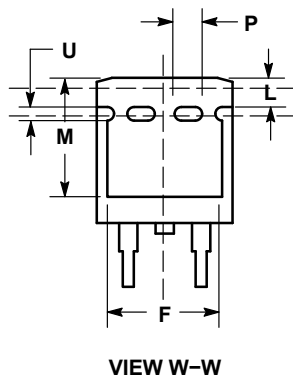
D²PAK 3 CASE 418B-04 ISSUE K



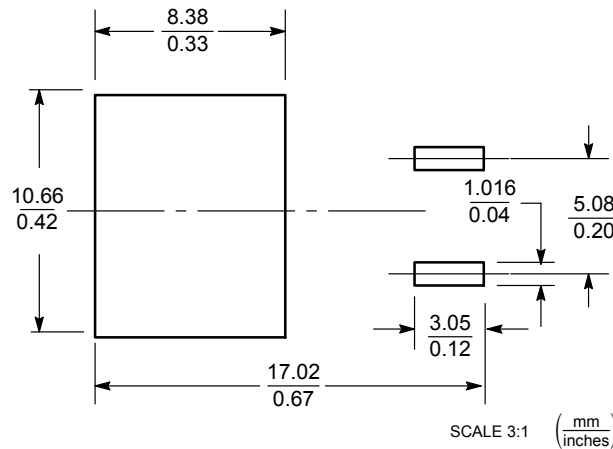
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

- STYLE 4:
1. GATE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR



SOLDERING FOOTPRINT*



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